

**Features :**

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications**

- Inverter
- Inductive heating
- Chopper

$V_{RSM}$	$V_{RRM}$	Type
900V	800V	Mx200DF80
1100V	1000V	Mx200DF100
1300V	1200V	Mx200DF120
1500V	1400V	Mx200DF140
1700V	1600V	Mx200DF160
1900V	1800V	Mx200DF180

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, $T_C=100^{\circ}C$	150			200	A
$I_{F(RMS)}$	RMS forward current					314	A
$I_{RRM}$	Repetitive peak current	at $V_{RRM}$	150			40	mA
$I_{FSM}$	Surge forward current	10ms half sine wave $V_R=0.6V_{RRM}$	150			5.5	kA
$I^2t$	$I^2t$ for fusing coordination					151	$A^2s \cdot 10^3$
$V_{FO}$	Threshold voltage		150			0.95	V
$r_F$	Forward slope resistance					0.90	m $\Omega$
$V_{FM}$	Peak forward voltage	$I_{FM}=600A$	25			1.55	V
$t_{rr}$	Reverse recovery time	$I_{FM}=200A, t_p=2000\mu s,$ $-di/dt=20A/\mu s, V_R=50V$	150			4.0	$\mu s$
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.180	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.040	$^{\circ}C/W$
$F_m$	Terminal connection torque(M8)				12.0		N·m
	Mounting torque(M6)				6.0		N·m
$V_{iso}$	Isolation voltage	50Hz, R.M.S, $t=1min, I_{iso}: 1mA(MAX)$		2500			V
$T_{vj}$	Junction temperature			-40		140	$^{\circ}C$
$T_{stg}$	Stored temperature			-40		125	$^{\circ}C$
$W_t$	Weight				810		g
Outline	M03						

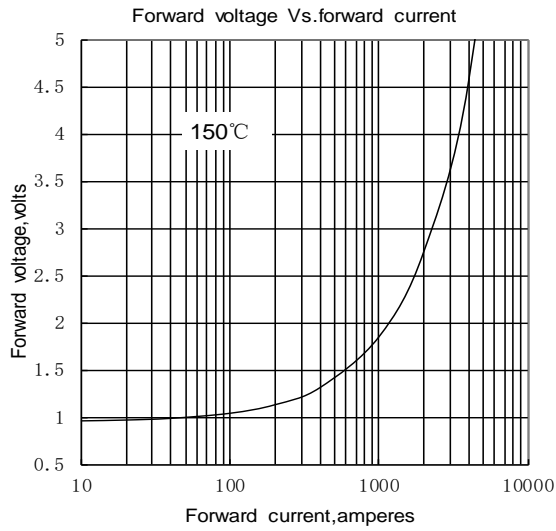


Fig.1

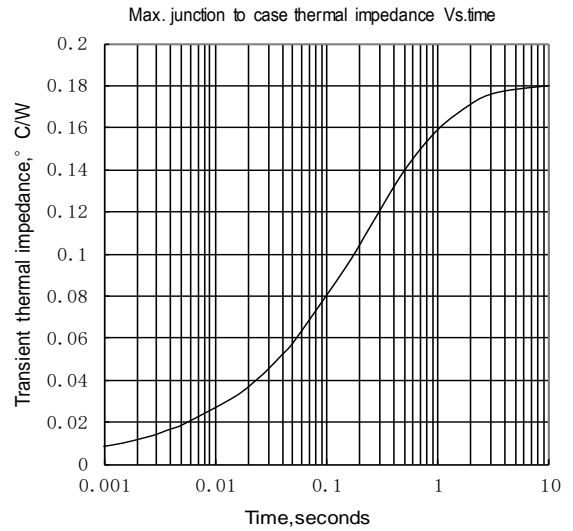


Fig.2

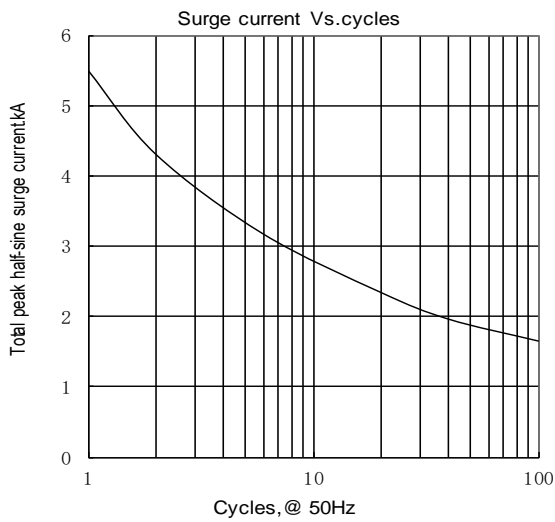


Fig.3

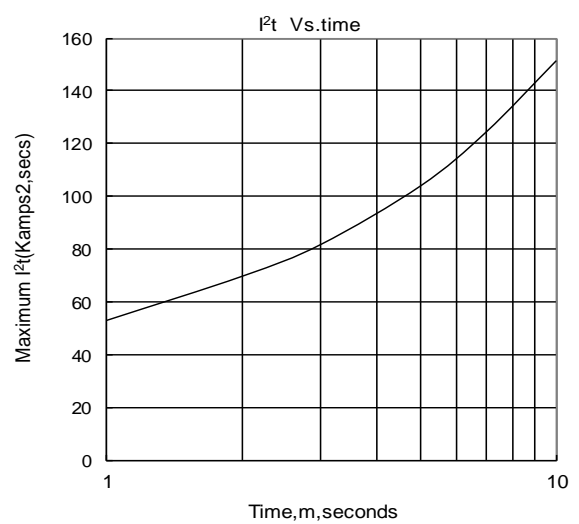


Fig.4

Outline:

